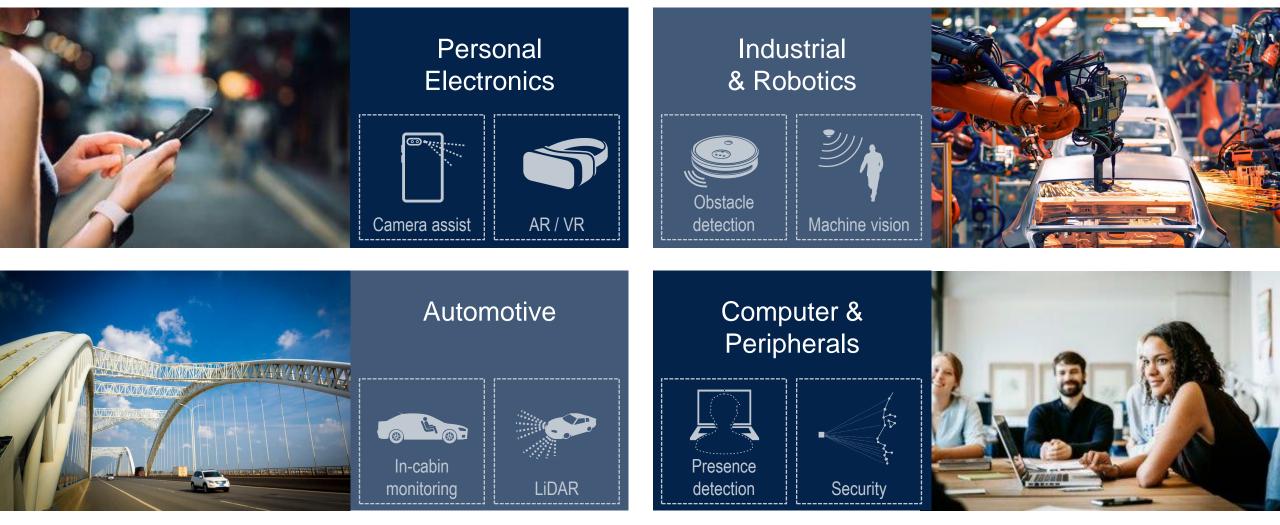




A low power, high dynamic range SPAD for sustainable sensing

Sara Pellegrini and Bruce Rae International SPAD Sensor Workshop 13th June 2022

Optical sensing solutions application domains







ST pioneer and leader in Time-of-Flight (ToF)

ST is #1 Worldwide ToF sensor supplier



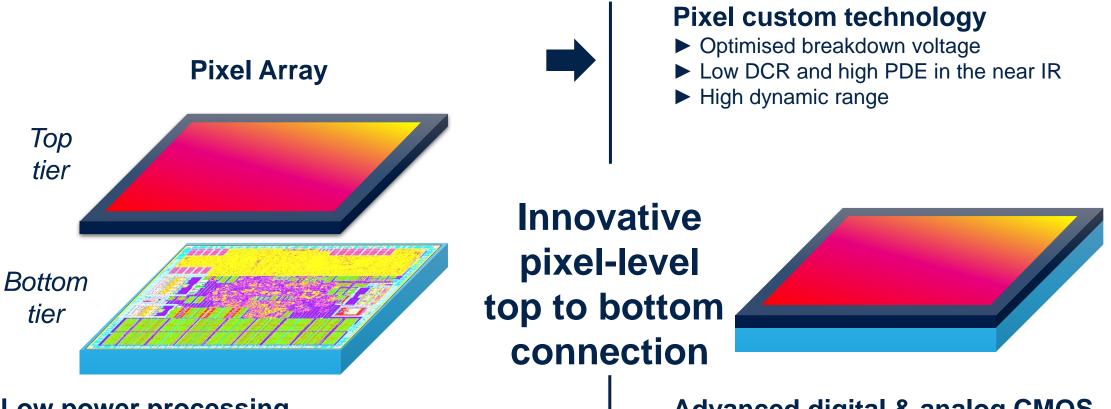


Unlimited Applications



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Wafer stacked CMOS image sensor



Low power processing

Integrating both low noise analogue and high speed, low power, digital logic



Advanced digital & analog CMOS

- ► High density & low power digital for efficient TDC
- Pixel-wide quench circuit implementation



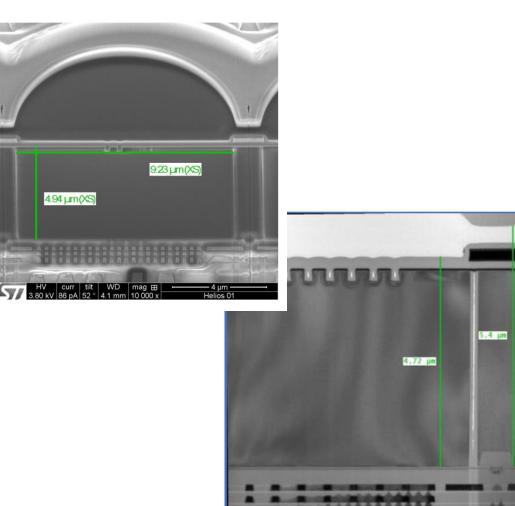
IMG140B-TOP technology | features

TOP tier process

SPAD photodiode 4.5 µm epitaxy for SPAD DTI for optical and electrical isolation Quench Resistor BSI Tungsten for shielding Microlens Structuration for QE enhancement

BOTTOM tier process

40nm CMOS Low power Dual gate oxide 7 metals levels Aligned with C40SPAD to allow IP reuse





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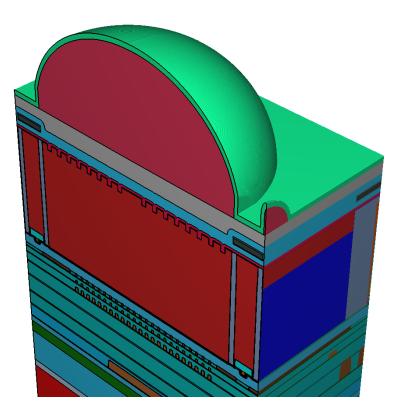
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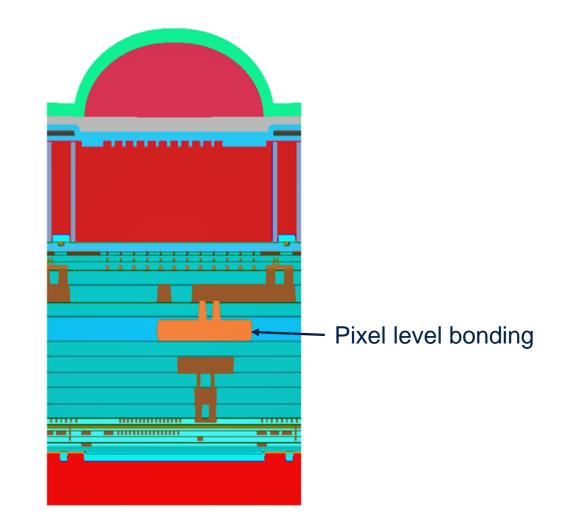
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The best of two worlds wafer stacked sensor

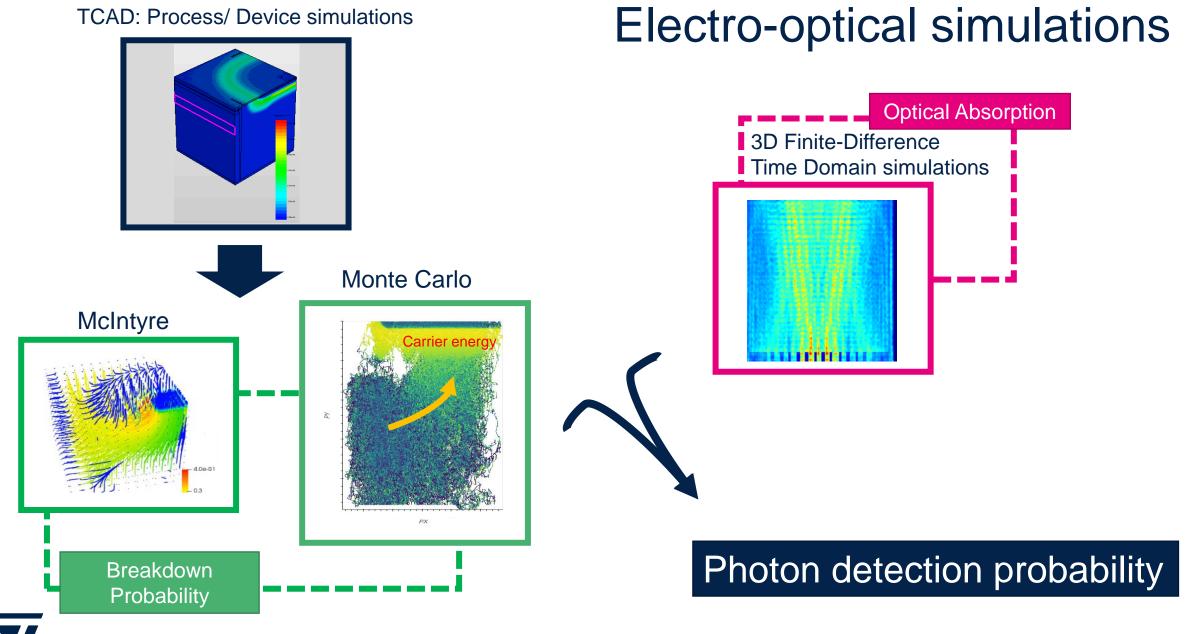
SPAD dedicated technology

- Bottom tier quench circuit for high FF
- Large collecting volume to maximise PDE





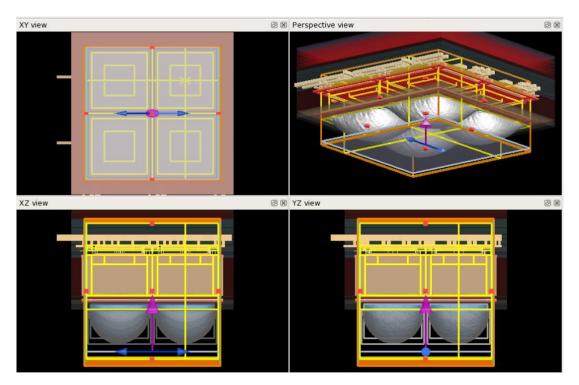




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Optical simulations: methodology

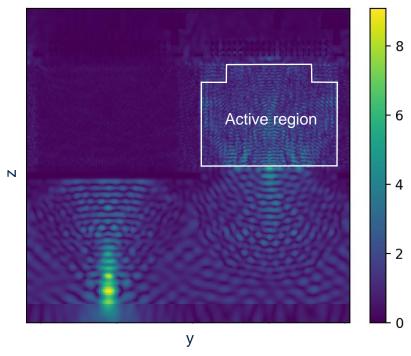
3D model of SPAD pixels:



Use 3D electromagnetic FDTD algorithm to solve Maxwell equations (Lumerical software)

Electromagnetic fields inside pixel

E (V/m)

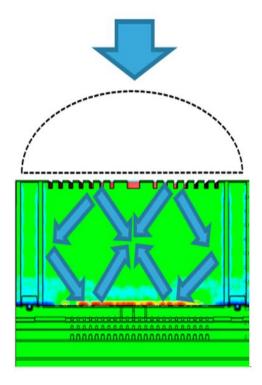


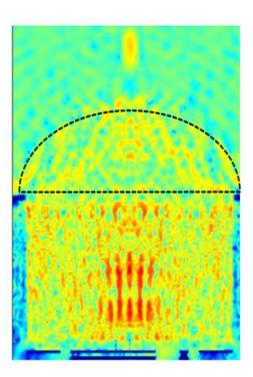
Extract optical absorption and crosstalk



Structuration design and simulation

3D architecture with structuration: multiple reflections → path length x N (with N>>2)

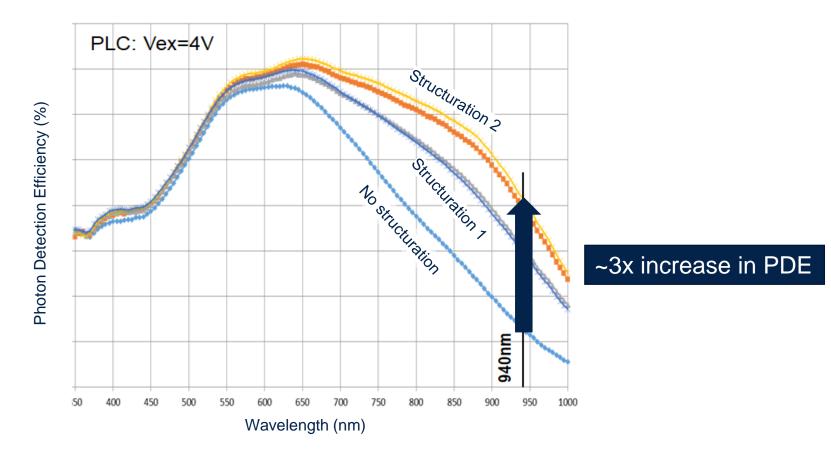






Structuration impact

3D architecture with structuration: multiple reflections → Photon detection efficiency improvement



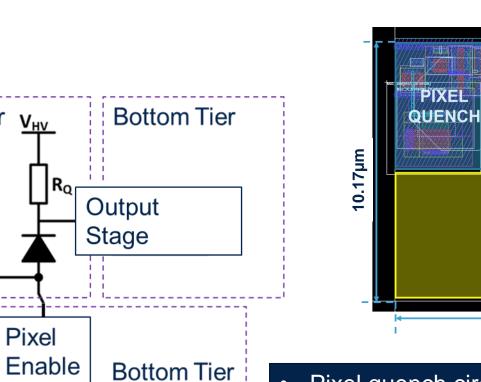


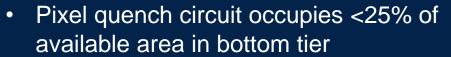
3D40SPAD - Pixel

b<mark>a_cen</mark>tre

AVAILABLE

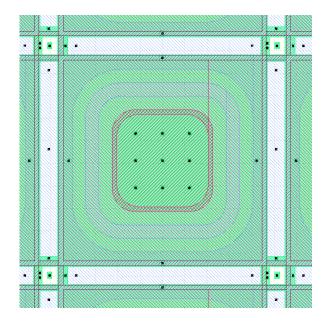
AREA





10.17µm

- GO1 compatible pixel output voltage •
- Positive Vbd compatible with efficient • on-chip charge pumping

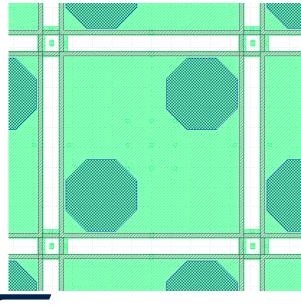


Top Tier V_{HV}

VPULLUP

Ror

Pixel



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Breakdown Voltage vs Temperature

Diode junction engineered to minimise Vbd → minimal power consumption

				20					
				19.5					
				19			(•	
VHV0			٤ ^{18.5}						
Temp [°C]	-20	60	80	0 <u>0</u> 18					
VHV0 [V]	17.0	18.9	19.6	→ 17.5					
HV0 is the minimum HV0 = Vbd + Vout_t	voltage for which t hresh	he SPAD pixel pr	oduces an output	17	•				

16.5

-40

-20

20

0

40

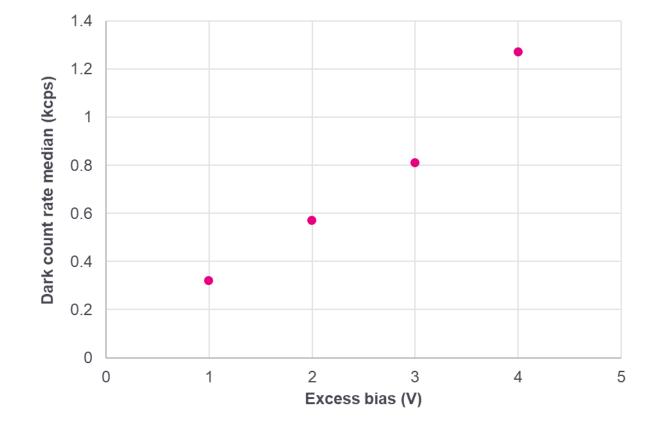
Temperature (°C)

60

80

100

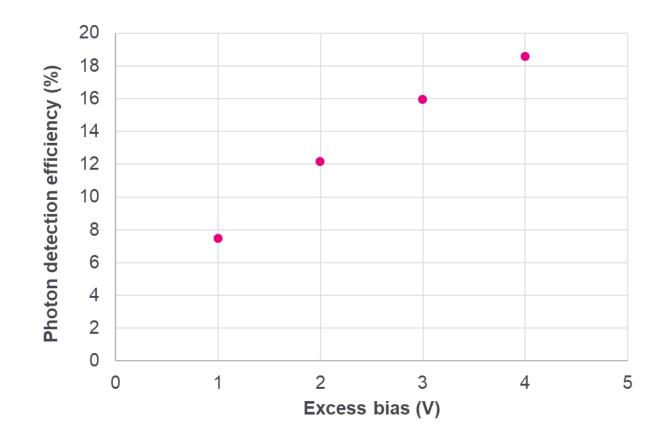
Dark count rate @ 60°C



Dark count rate					
Vexcess [V]	1 2		3	4	
DCR Med [kcps]	0.32	0.57	0.81	1.27	



Photon detection efficiency @ 60°C

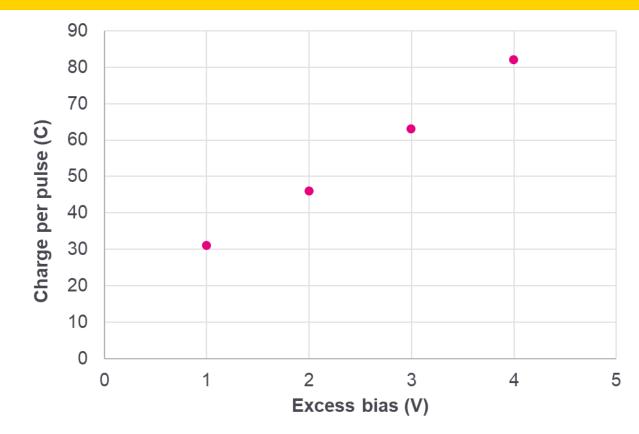


Photon Detection Efficiency						
Vexcess [V]	1 2		3	4		
PDE Median [%]	7.5	12.1	15.9	18.6		



Charge per pulse vs V excess (@ 60°C)

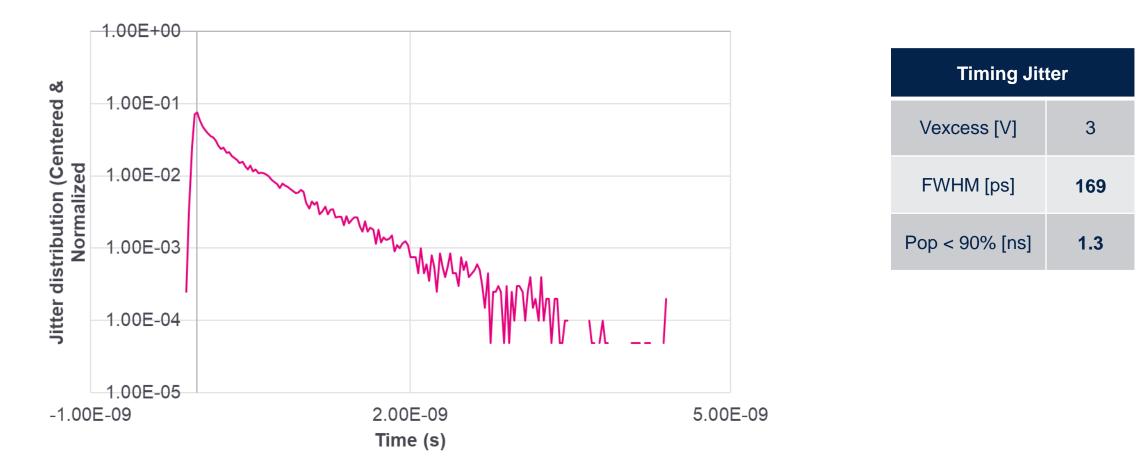
Low charge per pulse @ low VHV enables high resolution array and/or low array power consumption → In-line with ST sustainability strategy



Charge per pulse						
Vexcess [V]	1 2		3	4		
Charge per pulse [fC]	31	46	63	82		



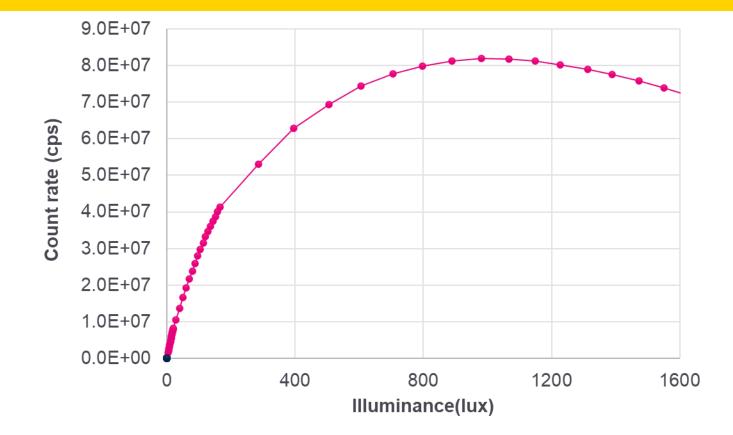
Timing jitter @ 60°C





Dynamic range @ 60°C

High QE diode requires high dynamic range pixel → maximise system benefit



Dead Time / Max Count Rate				
Vexcess [V]	3			
Max Count Rate [Mcps]	82			
Dead Time – 1/MCR [ns]	12.2			
Dead Time – 1/(e*MCR) [ns]	4.5			



Access to our advanced imaging technologies through foundry model

ST Imaging manufacturing & engineering know-how



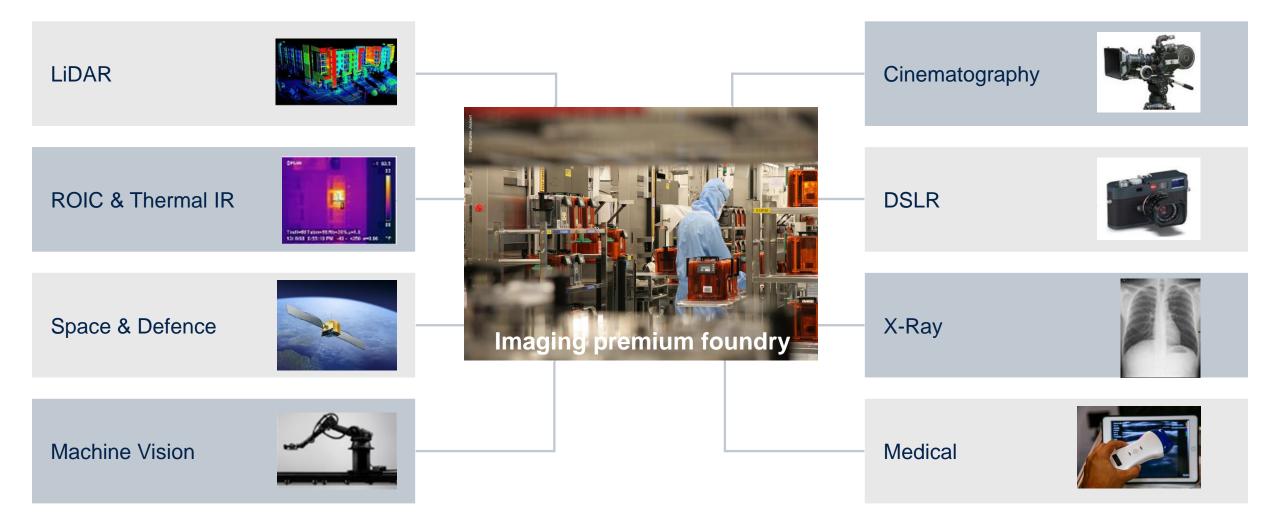
Billions imaging devices shipped World-class 12" wafer fabs Recognized expertise across Imaging value chain & ecosystem Premium services beyond traditional foundries



Access to differentiating technologies Reliable partner, flexible business model Benefit from broad imaging IP portfolio and expertise



Where to find us



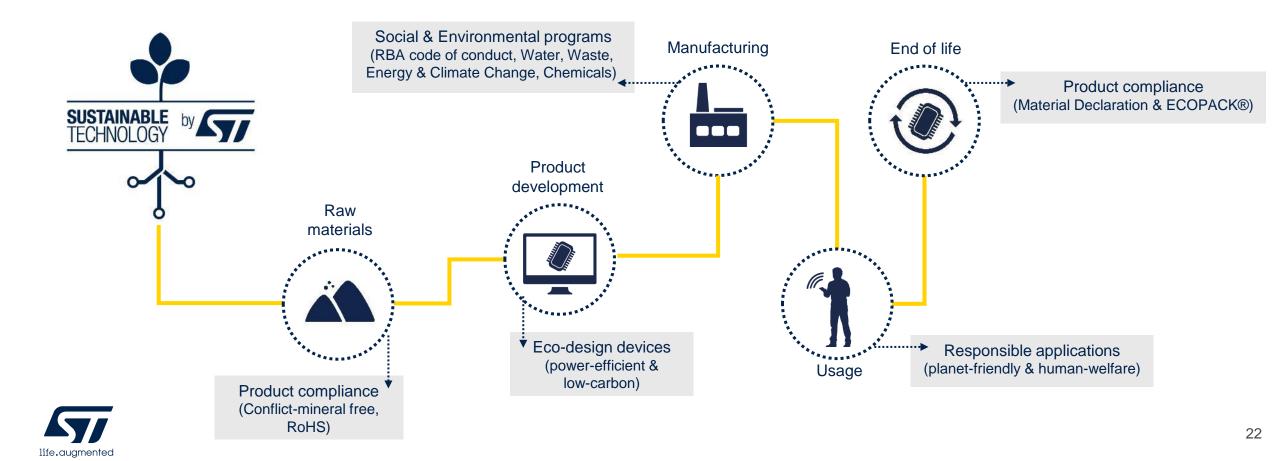


We are creators and makers of technology



Sustainable technology

Our Sustainable Technology program aims to develop responsible products which:
improve our social and environmental footprint at every stage of the product life
have the greatest positive impact on the planet and people in the end-application



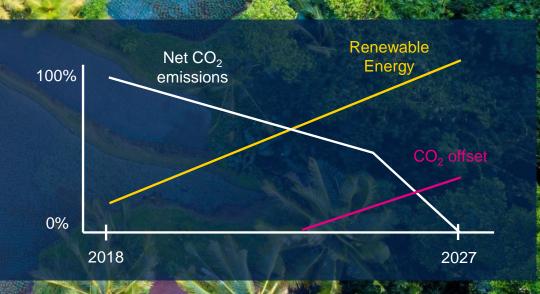
We will be carbon neutral by our 40th anniversary

Milestones

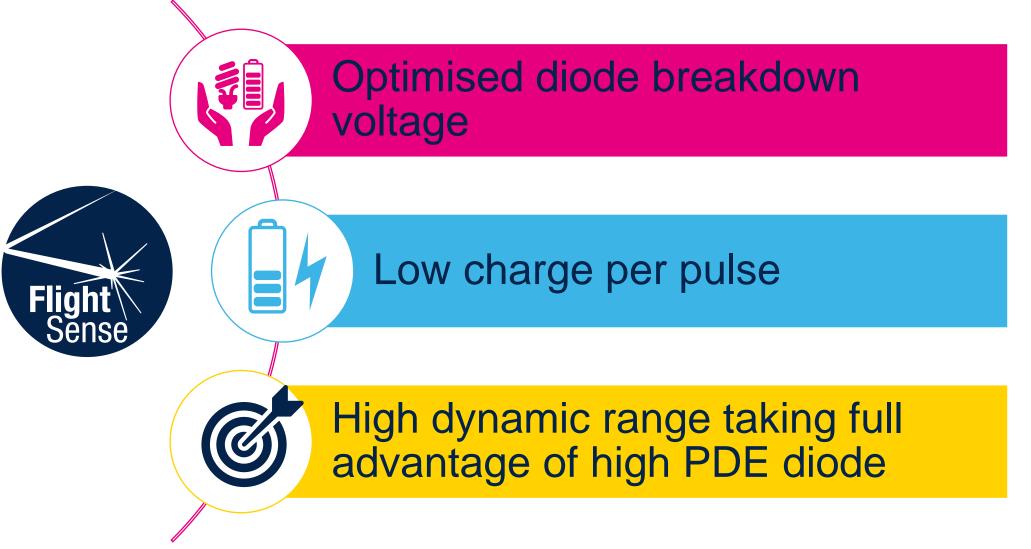
- Compliance with the 1.5°C scenario
 by 2025 recognized by SBTi
- Carbon neutral by 2027
- Sourcing 100% renewable energy by 2027

 Collaborative programs and partnerships for carbon neutrality throughout our ecosystems





Take aways





Acknowledgements

Imaging Division team in Edinburgh (UK) and Technology R&D team in Crolles (France) at STMicroelectronics

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Thank you!

